

**AD7510DI/AD7511DI**
**1.1 Scope.**

This specification covers the detail requirements for two monolithic dielectrically isolated CMOS switches featuring overvoltage protection up to  $\pm 25V$  above the power supplies. Both parts consist of four independent single pole single-throw analog switches differing only in that the digital control logic is inverted on the AD7511DI.

**1.2 Part Number.**

The complete part number per Table 1 of this specification is as follows:

Device	Part Number <sup>1</sup>
-1	AD7511DIS(X)/883B
-2	AD7510DIS(X)/883B
-3	AD7511DIT(X)/883B

**NOTE**

<sup>1</sup>See paragraph 1.2.3 for package identifier.

**1.2.3 Case Outline.**

See Appendix 1 of General Specification ADI-M-1000; package outline:

(X)	Package	Description
D	D-16	16-Pin Side-Brazed Ceramic
Q	Q-16	16-Pin Cerdip
E	E-20A	20-Contact LCC

**1.3 Absolute Maximum Ratings.** ( $T_A = 25^\circ C$  unless otherwise noted)

$V_{DD}$ to DGND	+17V
$V_{SS}$ to GND	-17V
Overvoltage at $V_D$ ( $V_S$ )	
(1 second surge)	$V_{DD} + 25V$ or $V_{SS} - 25V$
(Continuous)	$V_{DD} + 20V$ or $V_{SS} - 20V$
Switch Current ( $I_{DS}$ , Continuous)	50mA
1ms Duration, 10% Duty Cycle	150mA
Digital Input Voltage Range	-0.3V to $V_{DD} + 0.3V$
Power Dissipation	
Up to $+75^\circ C$	450mW
Derates above $+75^\circ C$	6mW/ $^\circ C$
Operating Temperature Range	$-55^\circ C$ to $+125^\circ C$
Storage Temperature Range	$-65^\circ C$ to $+150^\circ C$
Lead Temperature (Soldering 10sec)	$+300^\circ C$

**1.5 Thermal Characteristics.**

Thermal Resistance  $\theta_{JC} = 35^\circ C/W$   
 $\theta_{JA} = 120^\circ C/W$

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Table 1.

Test	Symbol	Device	Design Limit $T_{min}-T_{max}$	Sub Group 1	Sub Group 2, 3	Sub Group 4	Test Condition <sup>1</sup>	Units
Switch "ON" Resistance	$R_{ON}$	- 1, 2	175	100	175		$-10V \leq V_D \leq +10V, I_{DS} = 1mA$	$\Omega$ max
Leakage Current, Switch Open	$I_{DOFF}$	- 1, 2	200		200	3	$V_D = -10V, V_S = +10V$ and $V_D = +10V, V_S = -10V$	$\pm nA$ max
Output Current	$I_{DON}$	- 1, 2	400		400	10	$V_D = V_S = +10V$ and $V_D = V_S = -10V$	$\pm nA$ max
Digital Input Low Voltage	$V_{IL}$	- 1, 2	0.8	0.8	0.8			V max
Digital Input High Voltage	$V_{IH}$	- 1	3.0	3.0	3.0			V min
		- 2	2.4	2.4	2.4			
Input Leakage Current <sup>2</sup>	$I_{IN}$	- 1, 2	10	10			$V_{IN} = 0V$ or $V_{DD}$	$\pm nA$ max
Enable to Switch "ON" <sup>2</sup>	$t_{ON}$	- 1, 2	1.0				$V_{IN} = 0$ to $+3V$ and $+3V$ to $0V$	$\mu s$ max
Enable to Switch "OFF" <sup>2</sup>	$t_{OFF}$	- 1, 2	1.0					$\mu s$ max
Supply Current from $V_{DD}$	$I_{DD}$	- 1, 2	800	800	800		All Digital Inputs = $V_{IH}$	$\mu A$ max
			500	500	500		All Digital Inputs = $V_{IL}$	$\mu A$ max
Supply Current from $V_{SS}$	$I_{SS}$	- 1, 2	800	800	800		All Digital Inputs = $V_{IH}$	$\mu A$ max
			500	500	500		All Digital Inputs = $V_{IL}$	$\mu A$ max

NOTES

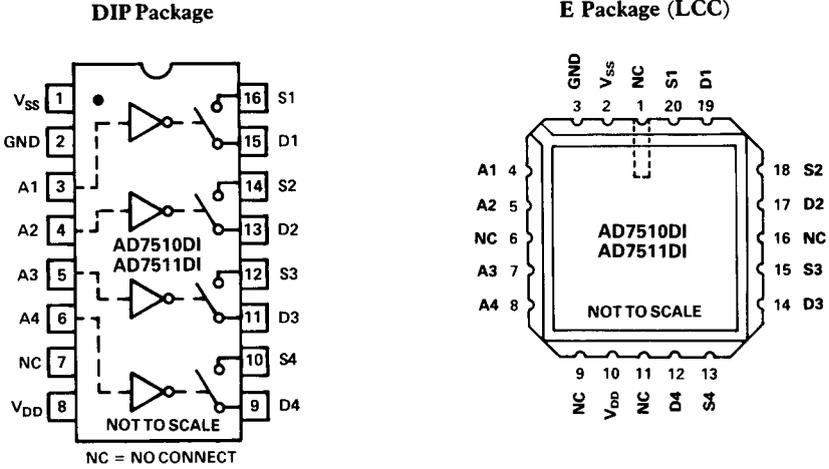
<sup>1</sup> $V_{DD} = +15V; V_{SS} = -15V$  unless otherwise stated.

<sup>2</sup>These design limits are at  $+25^\circ C$  only.

# AD7510DI/AD7511DI

## 3.2.1 Functional Block Diagram and Terminal Assignments.

### Top View

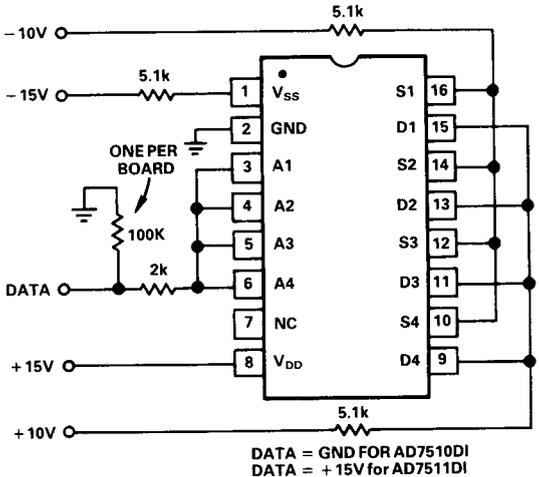


### 3.2.4 Microcircuit Technology Group.

This microcircuit is covered by technology group (82).

### 4.2.1 Life Test/Burn-In Circuit.

Steady state life test is per MIL-STD-883 Method 1005. Burn-in is per MIL-STD-883 Method 1015 test condition (B).



AD7510DI: SWITCH "ON" FOR ADDRESS "HIGH"  
 AD7511DI: SWITCH "ON" FOR ADDRESS "LOW"